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			Application Number		
			Filing Date		
			First Named Inventor	Arthur Kenneth Hochberg	
			Art Unit		
			Examiner Name		
Sheet	1	of	2	Attorney Docket Number	06417 USA

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
		US- 5,976,991	11/02/1999	Ravi K. Laxman, et al	
		US- 5,874,368	02/23/1999	Ravi K. Laxman, et al	
		US- 5,744,196	04/28/1998	Ravi K. Laxman, et al	
		US- 2002/0119327	08/29/2002	Barry C. Arkles, et al	
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NON PATENT LITERATURE DOCUMENTS			
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		G.E. MCGUIRE, Semiconductor Materials and Process Technology Handbook, Noyes Publication, 1988, pp. 289-301.	✓
		STANLEY WOLF, Silicon Processing for the VLSI Era, Lattice Press, 1990, Vol. II, pp. 20-22; 327-331.	✓
		TETSUJI SORITA, Mass Spectrometric and Kinetic Study of Low-Pressure..., J. Elect. Soc., 1994, Vol. 141, pp. 3505-3511.	✓
		B.A. SCOTT, Preparation of Silicon Nitride with Good Interface Properties..., Chemtronics, 1989, Vol. 4, pp. 231-234.	✓
		J.M. GROW, Growth Kinetics and Characterization of Low Pressure..., Elsevier Sci., 1995, Mat. Letters 23, pp. 187-193.	✓
		W.C. Yeh, Low-Temperature Chemical-Vapor-Deposition of Silicon-Nitride..., J. Appl. Phys., 1996, Vol. 35, pp. 1509-1512.	✓
		ARTHUR K. HOCHBERG, Diethylsilane As A Silicon Source for the Deposition..., Mat. Res. Soc. Symp., 1991, Vol. 204, pp. 509-514.	✓

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